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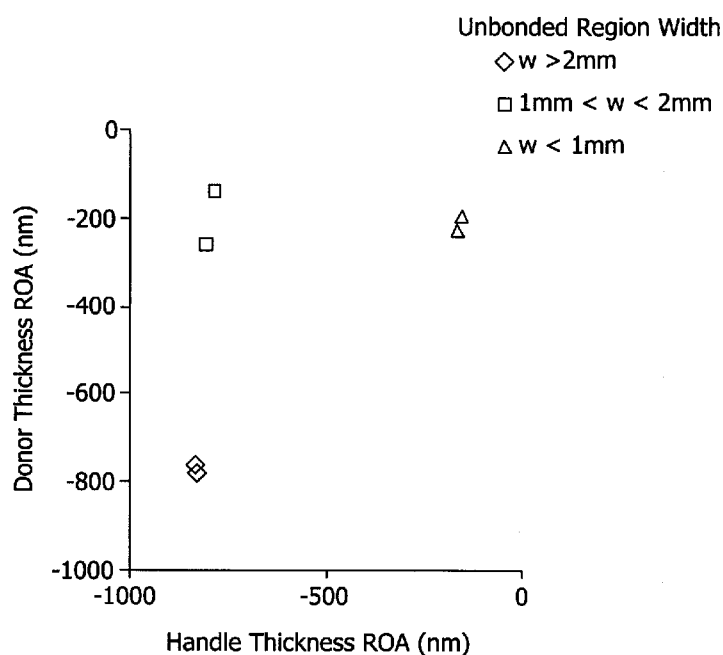
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(54) Title: METHODS FOR REDUCING THE WIDTH OF THE UNBONDED REGION IN SOI STRUCTURES AND
WAFERS AND SOI STRUCTURES PRODUCED BY SUCH METHODS**FIG. 7**(57) Abstract: The disclosure relates to prepa-
ration of silicon on insulator structures with re-
duced unbonded regions and to methods for
producing such wafers by minimizing the roll-
off amount (ROA) of the handle and donor
wafers. Methods for polishing wafers are also
provided.

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